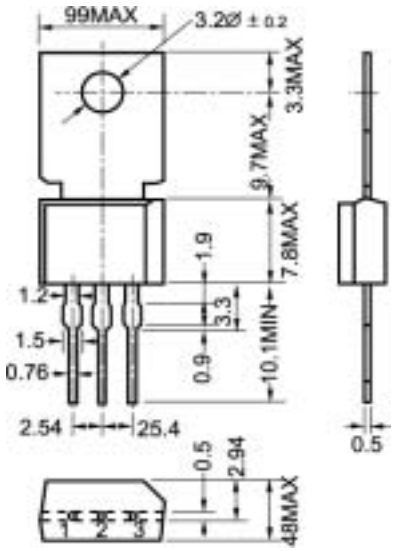
2P4M

PLASTIC MOLDED THYRISTOR

K A G



◆ Features

・With TO-202 package

・1cathode 2 anode 3 gate

◆ Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	400 (note:R_{GK}=1kΩ)	V
V_{RRM}	Repetitive peak reverse voltage	400 (note:R_{GK}=1kΩ)	V
$I_{T(AV)}$	On-state current	2(Tc=77℃, θ=180° Single phase(1/2wave)	A
I_{TSM}	Surge non-repetitive on-state current	20	A
P_{GM}	Peak gate power dissipation	0.5 (f ≥50Hz, Duty ≤10%)	W
$P_{G(AV)}$	Average gate power dissipation	0.1	W
I_{FGM}	Peak gate forward current	0.2 (f ≥50Hz, Duty ≤10%)	A
V_{RGM}	Peak gate reverse voltage	6	V
T_j	Junction temperature	-40 to + 125	℃

◆ Electrical characteristics (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	V_{RM}=V_{RRM},Tj=125℃,R_{GK}=1kΩ		100	μA
I_{DRM}	Repetitive peak off-state current	V_{DM}=V_{DRM},Tj=125℃,R_{GK}=1kΩ		100	μA
V_{TM}	On-state voltage	I_{TM}=4A		1.8	V
I_{GT}	Gate-trigger current	V_{DM}=6V;R_L=100Ω,R_{GK}=1kΩ		100	μA
V_{GT}	Gate-trigger voltage	V_{DM}=6V;R_L=100Ω,R_{GK}=1kΩ		0.8	V
V_{GD}	Gate non-trigger voltage	V_{DRM}=1/2V_{DRM},Tj=125℃,R_{GK}=1kΩ	0.2		V
I_H	Holding current	V_D=24V; R_{GK}=1kΩ,I_{TM}=4A		5	mA
$R_{th(j-c)}$	Thermal resistance	Junction to case		10	℃/W